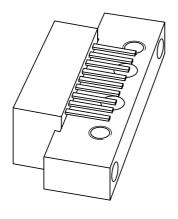
DISCRETE SEMICONDUCTORS

DATA SHEET



BGX885N 860 MHz, 17 dB gain push-pull amplifier

Product specification Supersedes data of 1997 Mar 26

2001 Nov 14





860 MHz, 17 dB gain push-pull amplifier

BGX885N

FEATURES

- · Excellent linearity
- · Extremely low noise
- Silicon nitride passivation
- Rugged construction
- Gold metallization ensures excellent reliability.

DESCRIPTION

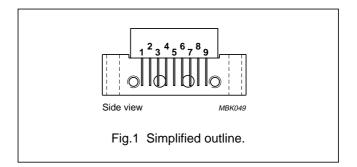
The BGX885N is a hybrid amplifier module designed for CATV/MATV systems operating over a frequency range of 40 to 860 MHz at a voltage supply of 24 V (DC).

PINNING - SOT115D

PIN	DESCRIPTION	
1	input; note 1	
2, 3	common	
4	60 mA supply terminal	
5, 6, 7	common	
8	+V _B	
9	output; note 1	

Note

1. Pins 1 and 9 carry DC voltages.



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
G _p	power gain	f = 50 MHz	16.5	17.5	dB
		f = 750 MHz	17.3	_	dB
I _{tot}	total current consumption (DC)	V _B = 24 V	_	240	mA

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V _B	DC supply voltage	_	26	V
Vi	RF input voltage	_	65	dBmV
T _{stg}	storage temperature	-40	+100	°C
T _{mb}	operating mounting base temperature	-20	+100	°C

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CHARACTERISTICS

Table 1 Bandwidth 40 to 860 MHz; $V_B = 24 \text{ V}$; $T_{mb} = 30 \,^{\circ}\text{C}$; $Z_S = Z_L = 75 \,^{\circ}\Omega$

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Gp	power gain	f = 50 MHz	16.5	17.5	dB
		f = 750 MHz	17.3	_	dB
SL	slope cable equivalent	f = 40 to 860 MHz	0.2	1.4	dB
FL	flatness of frequency response	f = 40 to 860 MHz	_	±0.3	dB
S ₁₁	input return losses	f = 40 MHz; note 1	20	_	dB
		f = 800 to 860 MHz	10	_	dB
S ₂₂	output return losses	f = 40 MHz; note 1	20	_	dB
		f = 640 to 860 MHz	15	-	dB
d ₂	second order distortion	note 2	_	-53	dB
Vo	output voltage	$d_{im} = -60 \text{ dB}$; note 3	61	_	dBmV
		$d_{im} = -60 \text{ dB}$; note 4	60	-	dBmV
NF	noise figure	f = 50 MHz	_	7.5	dB
		f = 350 MHz	_	7.5	dB
		f = 550 MHz	_	7.5	dB
		f = 650 MHz	_	7.5	dB
		f = 750 MHz	_	8	dB
		f = 860 MHz	_	8	dB
I _{tot}	total current consumption (DC)	note 5	_	240	mA

Notes

1. Decrease per octave of 1.5 dB.

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2. f_p = 349.25 \text{ MHz}; V_p = V_o = 59 \text{ dBmV}; \\ f_q = 403.25 \text{ MHz}; V_q = V_o; \\ \text{measured at } f_p + f_q = 752.5 \text{ MHz}.
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3. Measured according to DIN45004B:

```
\begin{split} f_p &= 341.25 \text{ MHz; } V_p = V_o; \\ f_q &= 348.25 \text{ MHz; } V_q = V_o - 6 \text{ dB;} \\ f_r &= 350.25 \text{ MHz; } V_r = V_o - 6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 339.25 \text{ MHz.} \end{split}
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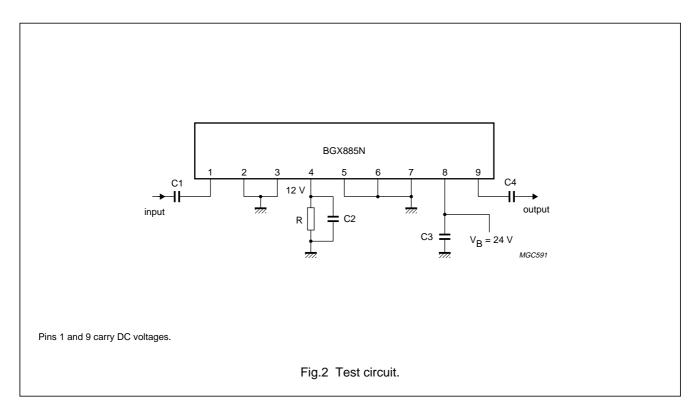
4. Measured according to DIN45004B:

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\begin{split} f_p &= 851.25 \text{ MHz; } V_p = V_o; \\ f_q &= 858.25 \text{ MHz; } V_q = V_o - 6 \text{ dB;} \\ f_r &= 860.25 \text{ MHz; } V_r = V_o - 6 \text{ dB;} \\ \text{measured at } f_p + f_q - f_r = 849.25 \text{ MHz.} \end{split}
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5. The module normally operates at $V_B = 24 \text{ V}$, but is able to withstand supply transients up to 30 V.

860 MHz, 17 dB gain push-pull amplifier

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List of components (see Fig.2)

COMPONENT	DESCRIPTION	VALUE
C1, C3, C4	ceramic multilayer capacitor	1 nF (max.)
C2	ceramic multilayer capacitor	1 nF
R	resistor	200 Ω, 1 W

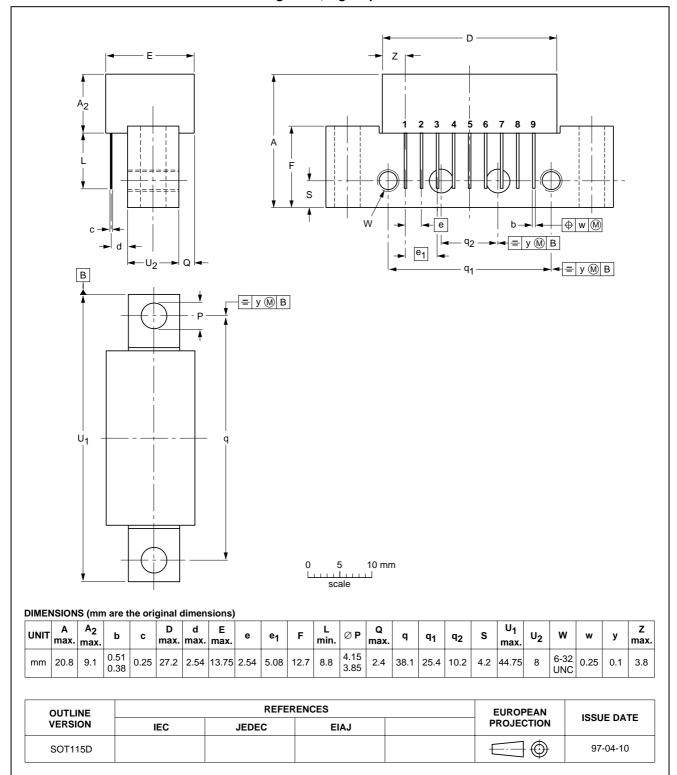
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PACKAGE OUTLINE

Rectangular single-ended package; aluminium flange; 2 vertical mounting holes; 2 x 6-32 UNC and 2 extra horizontal mounting holes; 9 gold-plated in-line leads

SOT115D



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DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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NOTES

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